

USSN 10/676,414

AMENDMENTS TO SPECIFICATION

ABSTRACT

A ferromagnetic data layer of a magnetic memory element is formed with a controlled nucleation site. In some embodiments, the nucleation site may be a divot in the data layer or a protrusion from the data layer. A Magnetic Random Access Memory ("MRAM") device may include an array of [such] magnetic memory elements having data layers with controlled nucleation sites.